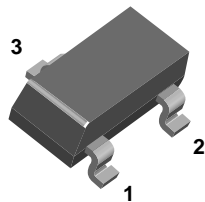


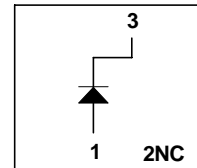
BAS29



SOT-23



Connection Diagram



Small Signal Diode

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{RRM}	Maximum Repetitive Reverse Voltage	120	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current		
	Pulse Width = 1.0 second	1.0	A
	Pulse Width = 1.0 microsecond	2.0	A
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_J	Operating Junction Temperature	150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C/W}$

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
V_R	Breakdown Voltage	$I_R = 1.0 \text{ mA}$	120		V
V_F^*	Forward Voltage	$I_F = 10 \text{ mA}$		0.75	V
		$I_F = 50 \text{ mA}$		0.84	V
		$I_F = 100 \text{ mA}$		0.90	V
		$I_F = 200 \text{ mA}$		1.00	V
		$I_F = 400 \text{ mA}$		1.25	V
I_R^*	Reverse Current	$V_R = 90 \text{ V}$		100	nA
		$V_R = 90 \text{ V}, T_A = 150^\circ\text{C}$		100	μA
C_T	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		2.0	pF
t_{rr}	Reverse Recovery Time	$I_F = I_R = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA}, R_L = 100 \Omega$		50	ns

*Pulse test: Pulse width=300us, Duty Cycle=2%